

Plastic Medium-Power Silicon PNP Transistor BD180G

This device is designed for use in 5.0 to 10 Watt audio amplifiers and drivers utilizing complementary or quasi complementary circuits.

Features

- High DC Current Gain
- BD180 is complementary with BD179
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	80	Vdc
Collector-Base Voltage	V _{CBO}	80	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector Current	I _C	1.0	Adc
Base Current	Ι _Β	2.0	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	30 240	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

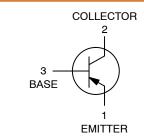
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	4.16	°C/W

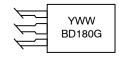
^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

3.0 AMPERES **POWER TRANSISTORS PNP SILICON** 80 VOLTS, 30 WATTS





MARKING DIAGRAM



= Year ww = Work Week BD180 = Device Code = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
BD180G	TO-225 (Pb-Free)	500 Units/Box

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Collector-Emitter Sustaining Voltage (Note 1) (I _C = 0.1 Adc, I _B = 0)	V _{(BR)CEO}	80	-	Vdc
Collector Cutoff Current (V _{CB} = 80 Vdc, I _E = 0)	Ісво	-	1.0	mAdc
Emitter Cutoff Current $(V_{BE} = 5.0 \text{ Vdc}, I_{C} = 0)$	I _{EBO}	-	1.0	mAdc
DC Current Gain (I _C = 0.15 A, V _{CE} = 2.0 V) (I _C = 1.0 A, V _{CE} = 2.0 V)	h _{FE}	40 15	250 -	-
Collector-Emitter Saturation Voltage (Note 1) (I _C = 1.0 Adc, I _B = 0.1 Adc)	V _{CE(sat)}	-	0.8	Vdc
Base-Emitter On Voltage (Note 1) (I _C = 1.0 Adc, V _{CE} = 2.0 Vdc)	V _{BE(on)}	-	1.3	Vdc
Current–Gain – Bandwidth Product ($I_C = 250 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ MHz}$)	f _T	3.0	-	MHz

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

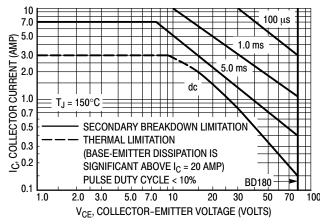


Figure 1. Active Region Safe Operating Area

The Safe Operating Area Curves indicate $I_C - V_{CE}$ limits below which the device will not enter secondary breakdown. Collector load lines for specific circuits must fall within the applicable Safe Area to avoid causing a catastrophic failure. To insure operation below the maximum T_J , power–temperature derating must be observed for both steady state and pulse power conditions.

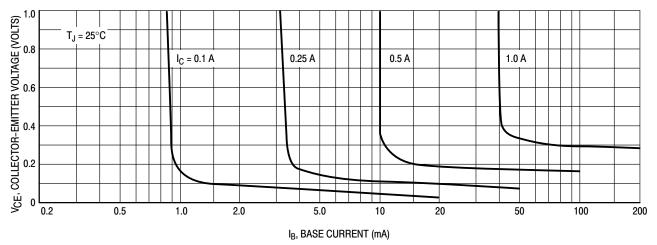
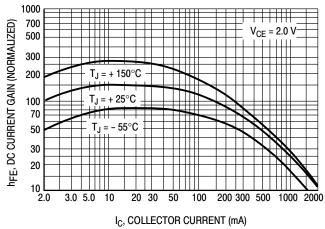


Figure 2. Collector Saturation Region

BD180G

1.2

 $T_J = 25^{\circ}C$



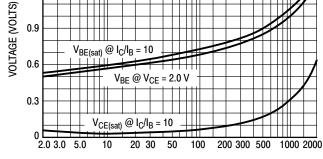


Figure 3. Current Gain

I_C, COLLECTOR CURRENT (mA) **Figure 4. "On" Voltages**

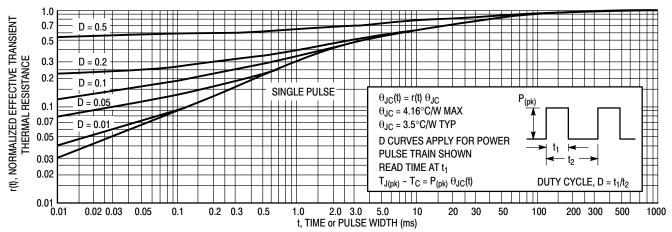
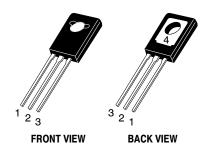


Figure 5. Thermal Response

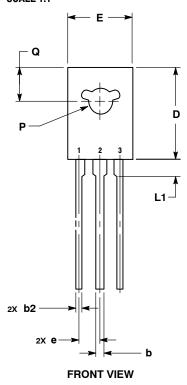
MECHANICAL CASE OUTLINE

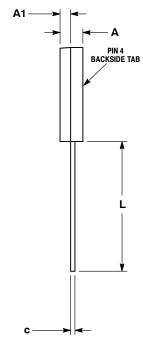


TO-225 CASE 77-09 **ISSUE AD**

DATE 25 MAR 2015

SCALE 1:1



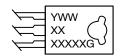


SIDE VIEW

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. NUMBER AND SHAPE OF LUGS OPTIONAL.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.40	3.00		
A1	1.00	1.50		
b	0.60	0.90		
b2	0.51	0.88		
С	0.39	0.63		
D	10.60	11.10		
E	7.40	7.80		
е	2.04	2.54		
L	14.50	16.63		
L1	1.27	2.54		
P	2.90	3.30		
Q	3.80 4.20			

GENERIC MARKING DIAGRAM*



= Year ww = Work Week XXXXX = Device Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

2., 4. DRAIN 3. GATE

= Pb-Free Package

	EMITTER COLLECTOR BASE	2., 4.	CATHODE ANODE GATE	STYLE 3: PIN 1. 2., 4. 3.	COLLECTOR	,	ANODE 1 ANODE 2 GATE	STYLE 5: PIN 1. 2., 4. 3.	
STYLE 6: PIN 1.	CATHODE	STYLE 7: PIN 1.	MT 1	STYLE 8: PIN 1.	SOURCE	STYLE 9: PIN 1.	GATE	STYLE 10: PIN 1.	SOURCE

2., 4. GATE 3. DRAIN

DRAIN

2., 4. 3. DRAIN

2., 4. GATE 3. MT 2

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2., 4. 3. GATE

ANODE

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